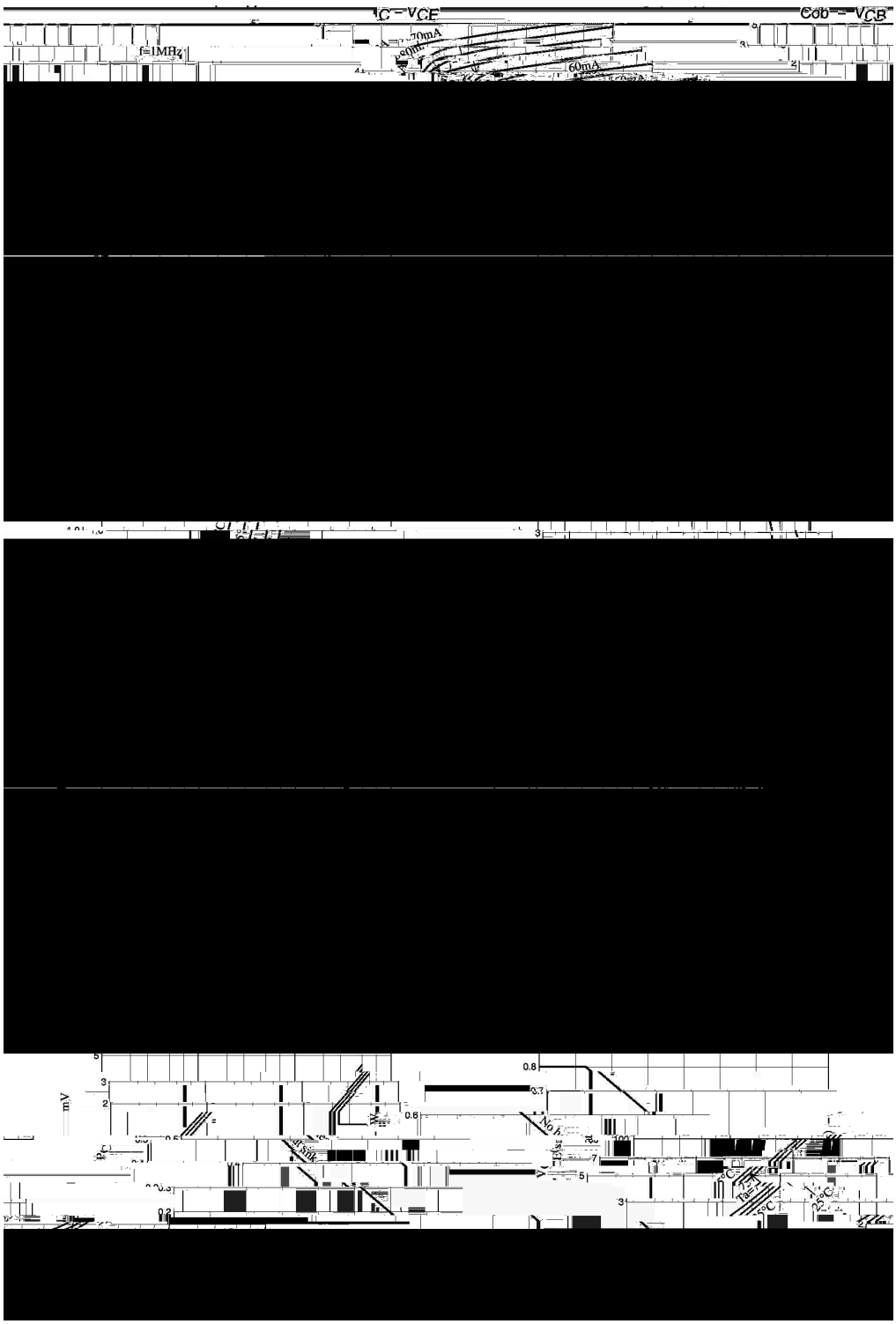
TO-220	NPN	Silicon NPN transistor in a TO-220 Plastic Package.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	50	V
Collector to Emitter Voltage	V_{CES}	80	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	5.0	A
Peak Collector Current	I_{CP}	7.5	A
Base Current - Continuous	I_B	1.2	A
Collector Power Dissipation	P_C	2	W
	$P_C(T_C=25\ \ )$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

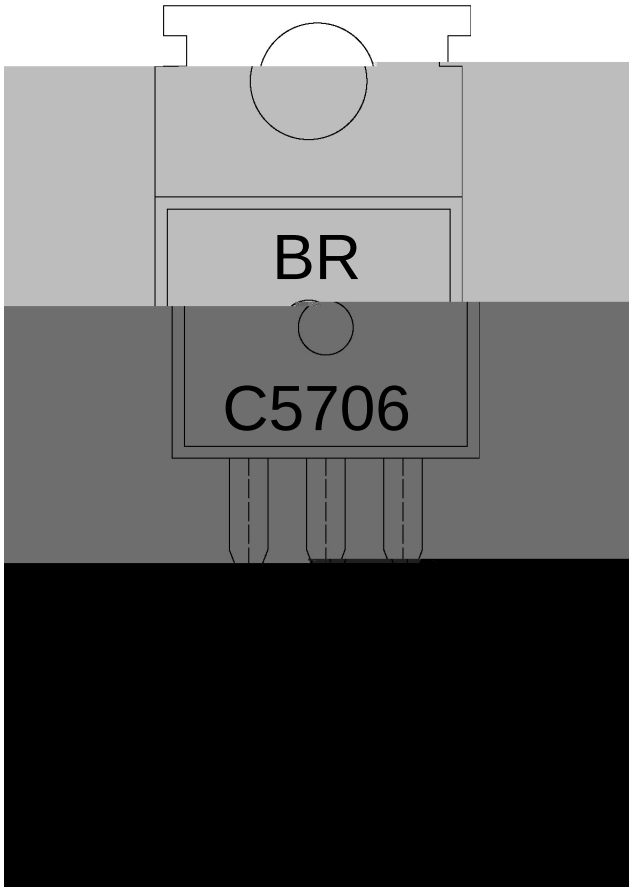
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.01mA I_E=0	80			V
Collector to Emitter Breakdown Voltage	V_{CES}	I_C=0.1mA R_{BE}=0	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA R_{BE}=∞	50			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_C=0.01mA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=40V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=0.5A	200		560	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=1.0A I_B=0.05A		0.09	0.135	V
	$V_{CE(sat)(2)}$	I_C=2.0A I_B=0.1A		0.16	0.24	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	V_{CE}=2.0V I_C=0.1A		0.89	1.2	V

/ Electrical Characteristic Curve



2SC5706

/ Marking Instructions



BR

C5706

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Note:

BR:	Company Code
C5706:	Product Type.
****:	Lot No. Code, code change with Lot No.